

LNA2801L

GaAlAs on GaAs Infrared Light Emitting Diode

For optical control systems

■ Features

- High-power output, high-efficiency: $I_e = 6 \text{ mW/sr}$ (min.)
- Emitted light spectrum suited for silicon photodetectors
- Good radiant power output linearity with respect to input current
- $\phi 3$ plastic package

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Power dissipation	P_D	75	mW
Forward current	I_F	50	mA
Pulse forward current *	I_{FP}	1	A
Reverse voltage	V_R	3	V
Operating ambient temperature	T_{opr}	-25 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +100	$^\circ\text{C}$

Note) *: $f = 100 \text{ Hz}$, Duty cycle = 0.1%

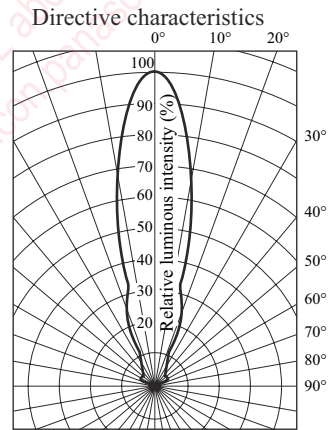
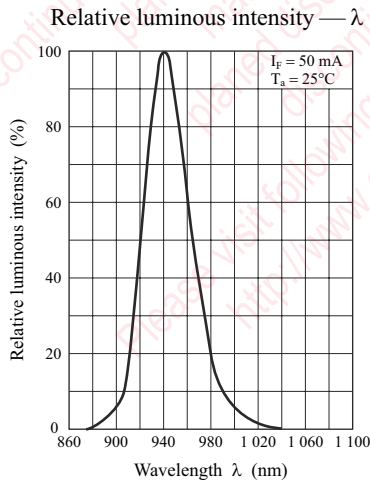
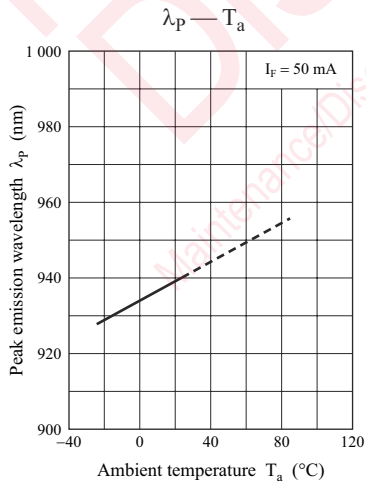
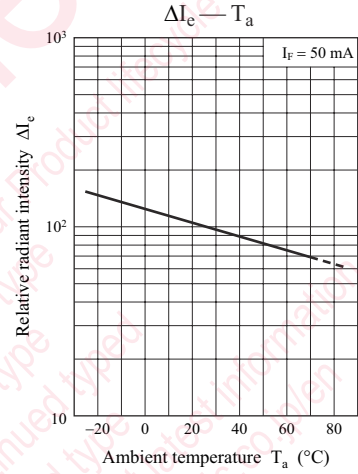
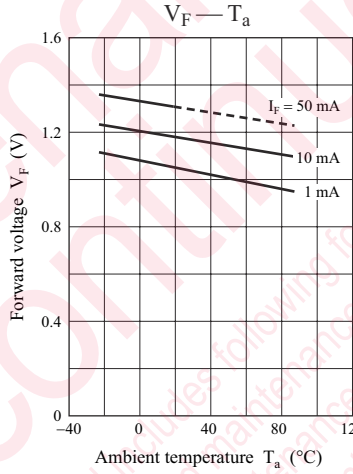
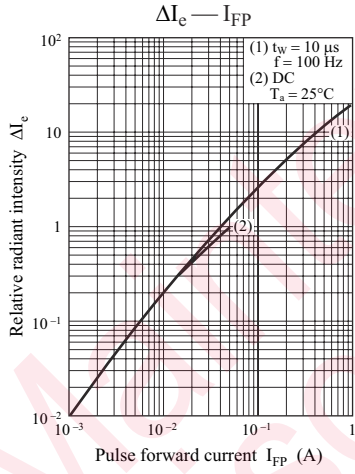
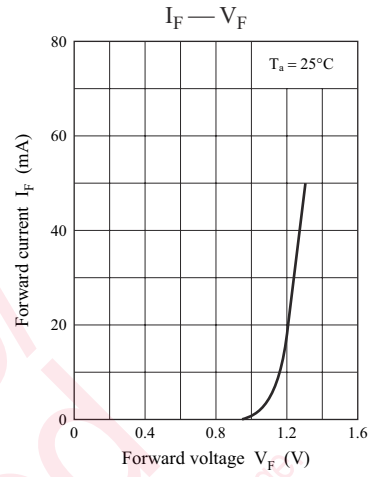
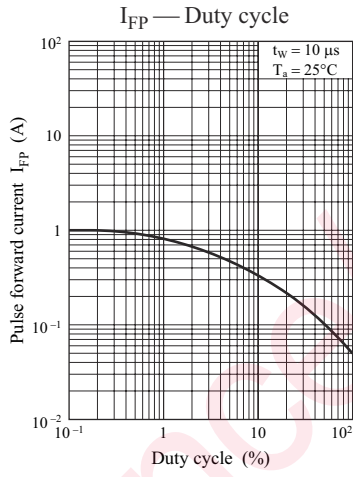
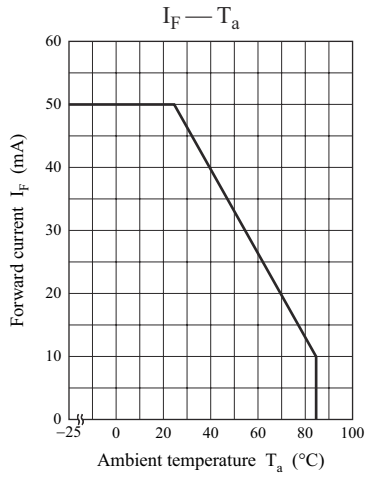
■ Electro-Optical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Center radiant intensity	I_e	$I_F = 20 \text{ mA}$	6.0			mW/sr
Reverse current	I_R	$V_R = 3 \text{ V}$			10	μA
Forward voltage	V_F	$I_F = 50 \text{ mA}$		1.3	1.5	V
Terminal capacitance	C_t	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$		35		pF
Peak emission wavelength	λ_p	$I_F = 50 \text{ mA}$		940		nm
Spectral half band width	$\Delta\lambda$	$I_F = 50 \text{ mA}$		50		nm
Half-power angle	θ	The angle when the center radiant intensity is halved.		15		$^\circ$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

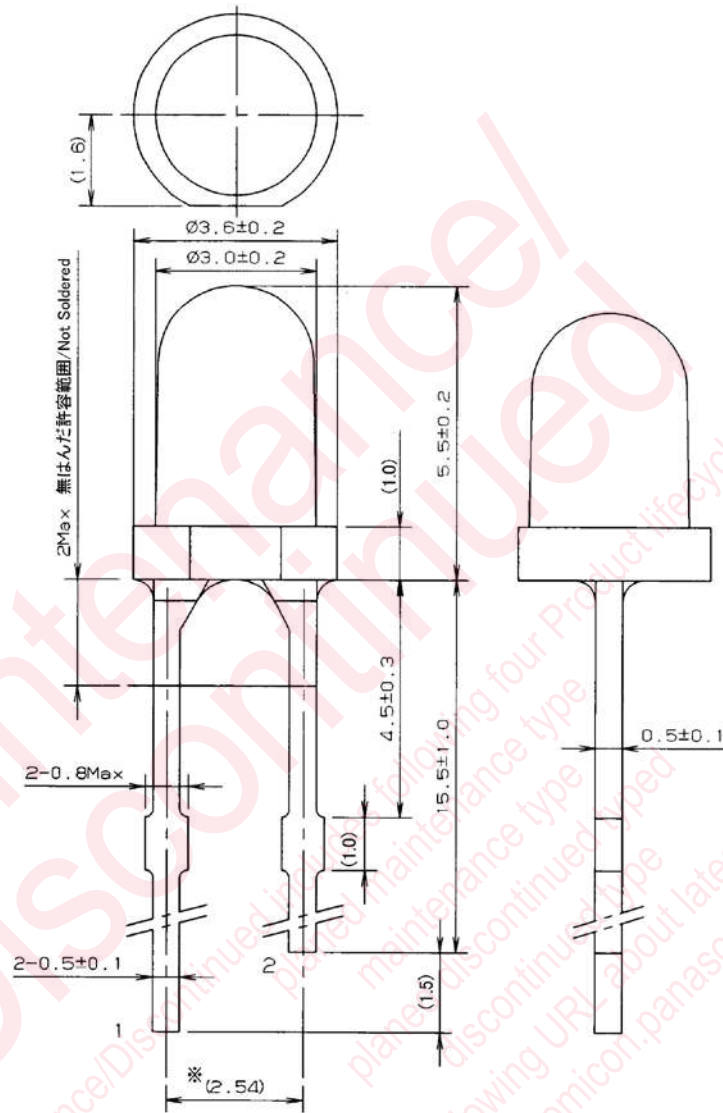
2. Cutoff frequency: 1 MHz

$$f_c : 10 \times \log \frac{P_O \text{ at } f = f_c}{P_O \text{ at } f = 50 \text{ kHz}} = -3$$



■ Package (Unit: mm)

LEXLTN2S0006



- Pin name
- 1: Anode
- 2: Cathode

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